

DOCUMENT-IDENTIFIER: US 20020135954 A1

TITLE: Magnetoresistive head and perpendicular magnetic recording-reproducing apparatus

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Detail Description Paragraph - DETX (58):

[0091] Examples of materials used for the antiferro-magnetic layers include a PtMn alloy, a PtPdMn alloy, a CrMn alloy, a CrPtMn alloy, an IrMn alloy and an RhMn alloy. The patterned antiferromagnetic layers can be formed by the following methods. (i) After deposition of an antiferromagnetic material, resist patterning is performed by photolithography, and then ion milling is performed with using the resist pattern as a mask to form patterned antiferromagnetic layers, followed by removing the resist pattern. (ii) Resist patterning is performed by photolithography, followed by removing a part of the protective layer on the free layer and subsequently depositing an antiferromagnetic layer. Then, the resist pattern and the antiferromagnetic layer thereon are removed by a lift-off method to form patterned antiferromagnetic layers.